

Device Modeling Report

COMPONENTS: Power MOSFET (Model Parameters)
PART NUMBER: TPCA8003-H
MANUFACTURER: TOSHIBA
Body Diode (Model Parameters) / ESD Protection Diode



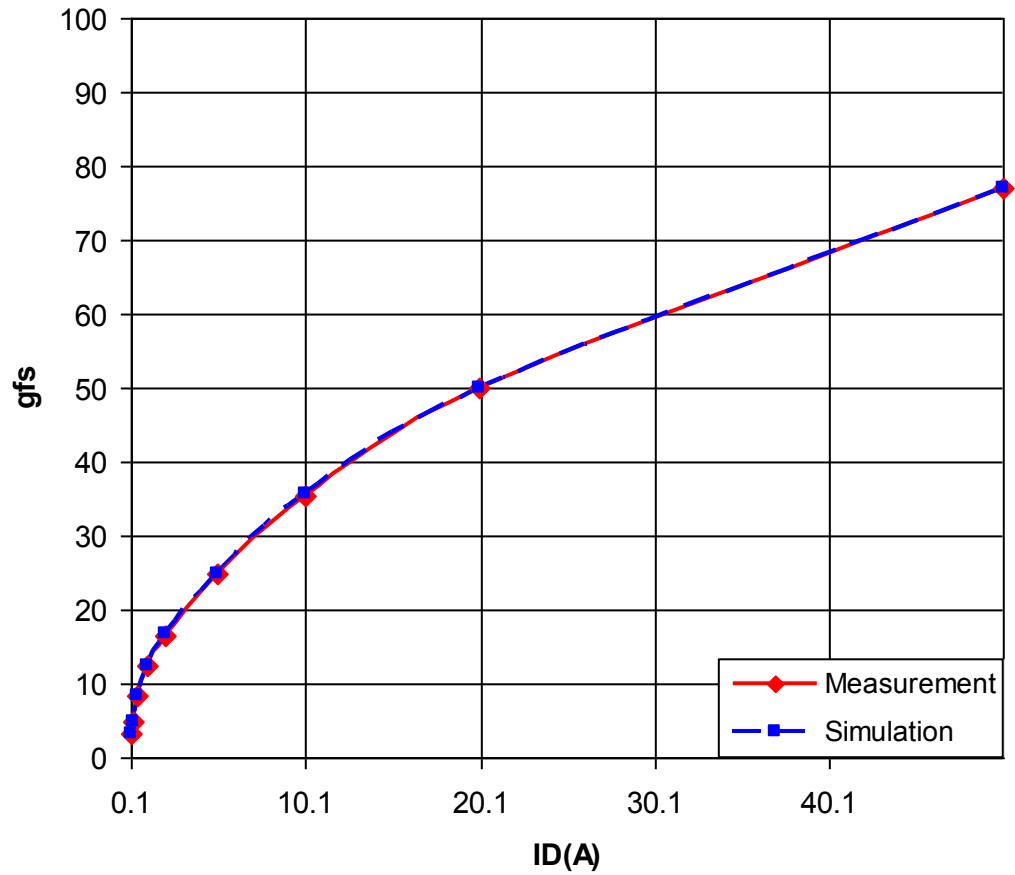
Bee Technologies Inc.

MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

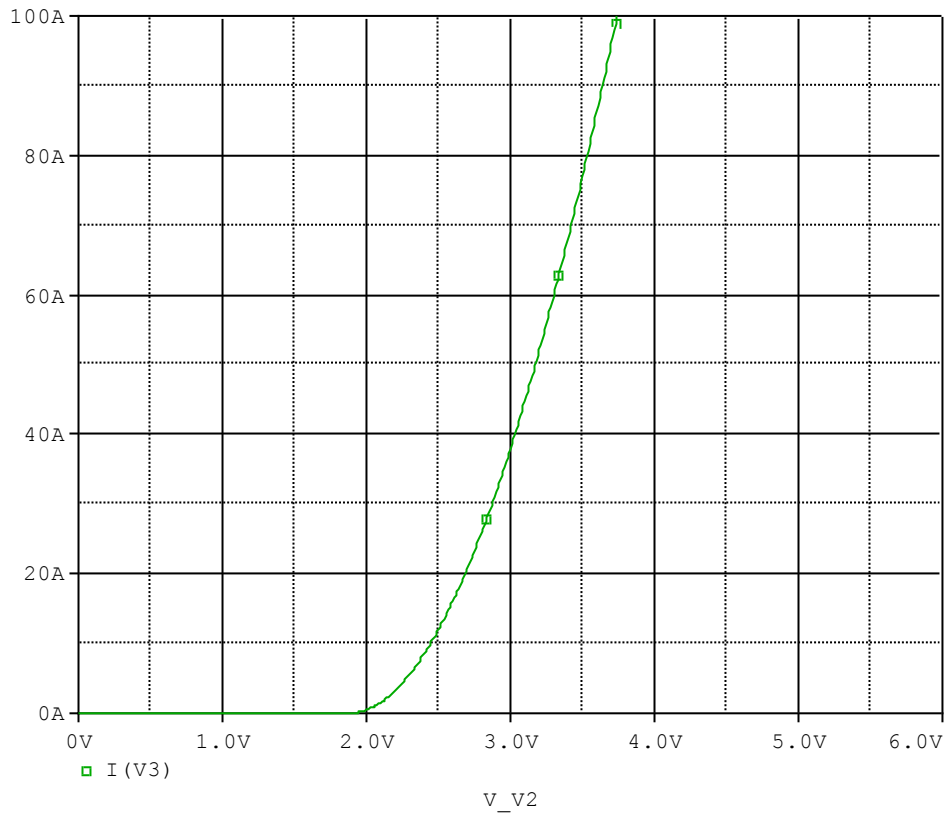


Comparison table

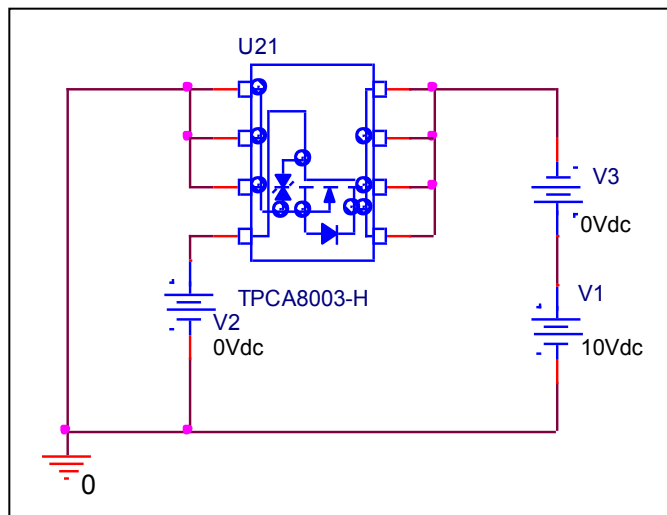
Id(A)	gfs		Error(%)
	Measurement	Simulation	
0.1	3.300	3.333	1.000
0.2	5.000	5.000	0.000
0.5	8.3.00	8.333	0.398
1	12.500	12.500	0.000
2	16.500	16.667	1.012
5	25.000	25.000	0.000
10	35.500	35.714	0.603
20	50.000	50.000	0.000

V_{gs}-I_d Characteristic

Circuit Simulation result

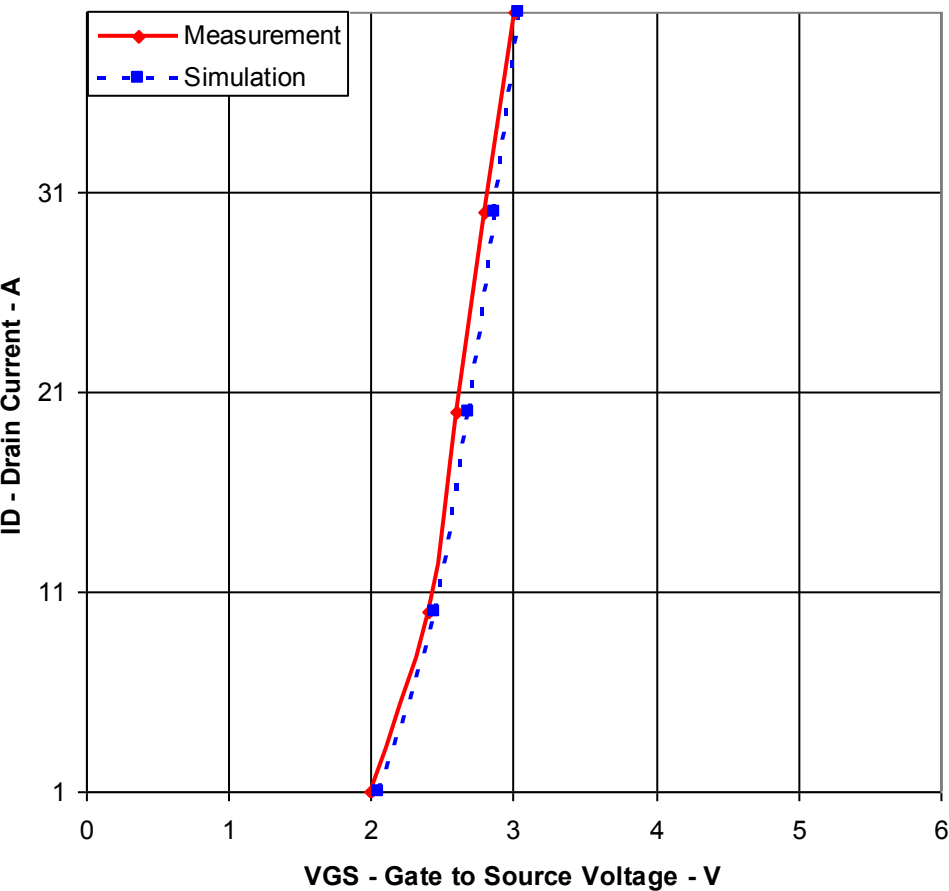


Evaluation circuit



Comparison Graph

Circuit Simulation Result

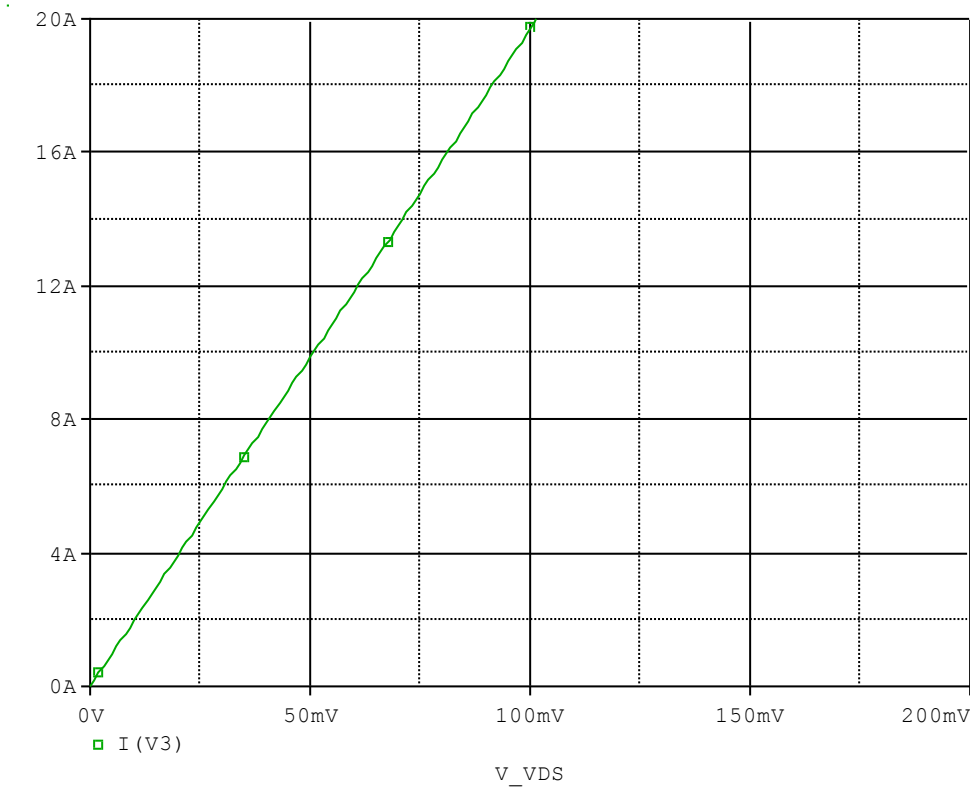


Simulation Result

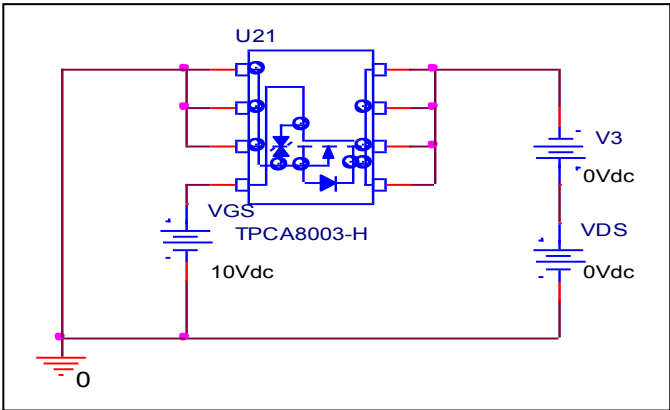
ID(A)	VGS(V)		Error (%)
	Measurement	Simulation	
1	2.000	2.057	2.850
10	2.400	2.447	1.958
20	2.600	2.684	3.231
30	2.800	2.871	2.536
40	3.000	3.030	1.000

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

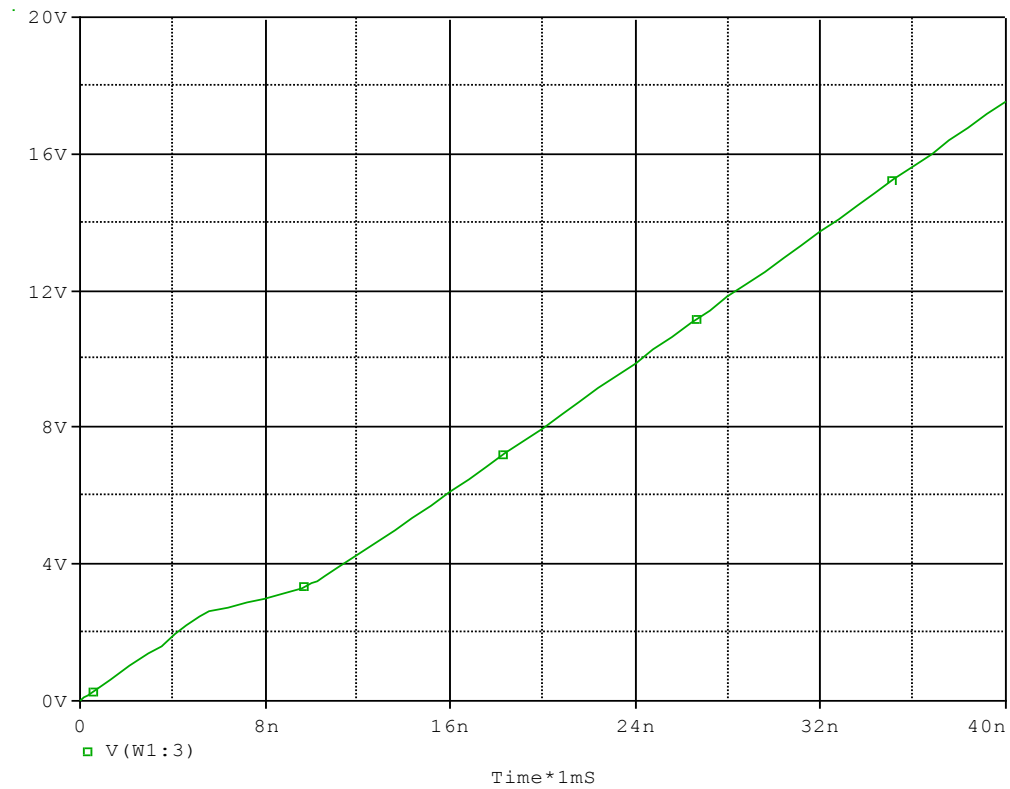


Simulation Result

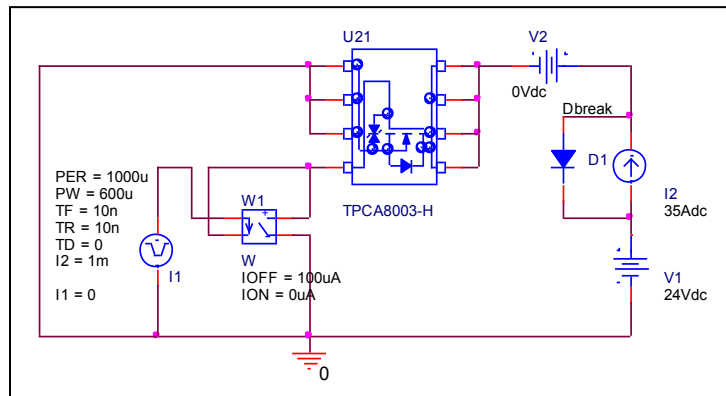
I_D=18A, V_{GS}=10V	Measurement		Simulation		Error (%)
R_{DS} (on)	5.100	Ω	5.075	Ω	-0.490

Gate Charge Characteristic

Circuit Simulation result



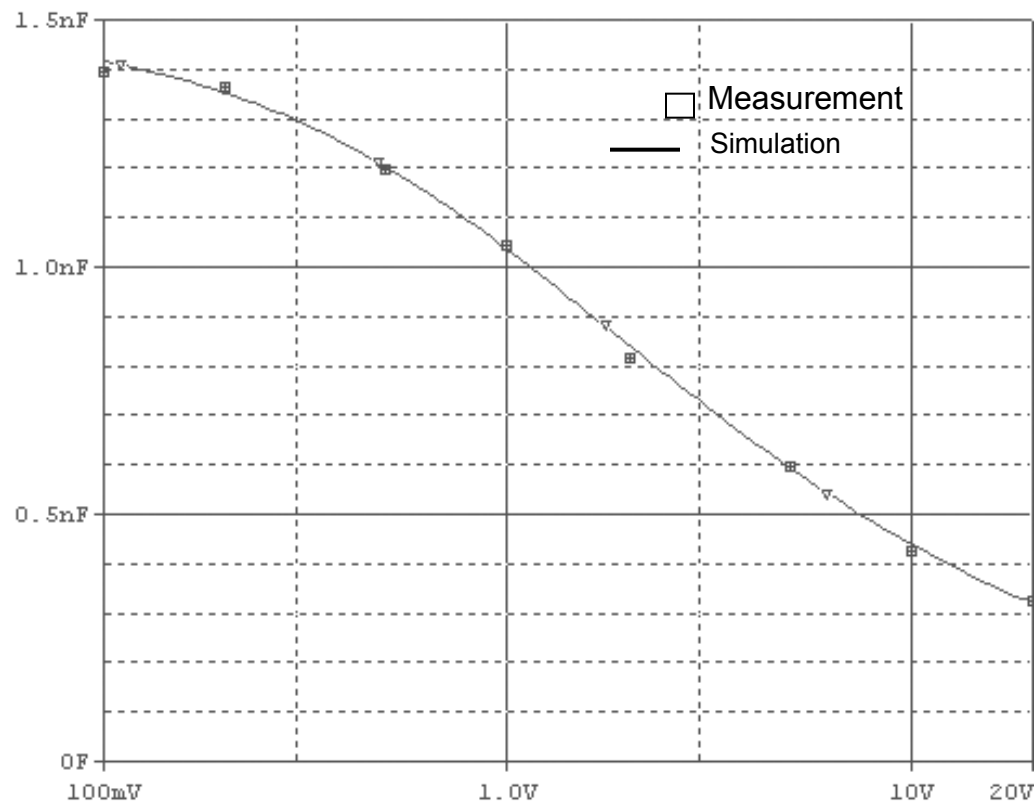
Evaluation circuit



Simulation Result

$V_{DD}=240V, I_D=35A$ $, V_{GS}=10V$	Measurement	Simulation	Error (%)
Q_{gs}(nC)	5.800	5.789	-0.190
Q_{gd}(nC)	5.100	5.087	-0.255
Q_g	25.000	24.262	-2.952

Capacitance Characteristic

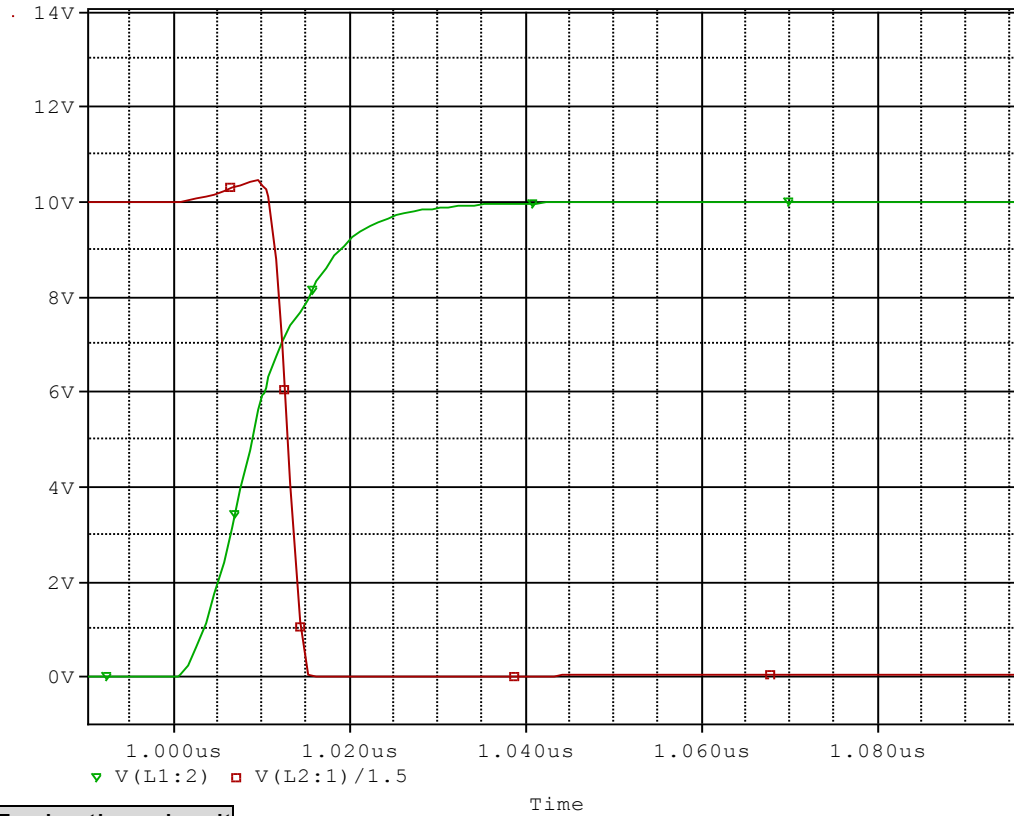


Simulation Result

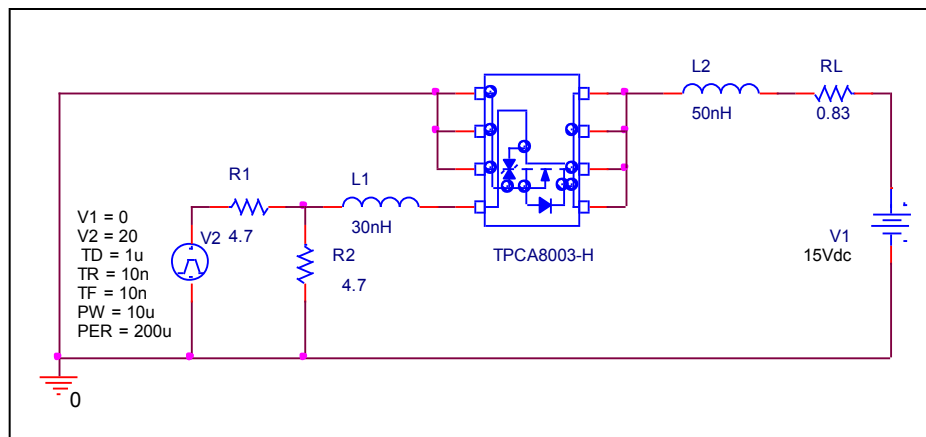
V _{DS} (V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.1	1400	1430.000	2.143
0.2	1370	1350.000	-1.460
0.5	1200	1208.000	0.667
1	1050	1045.000	-0.476
2	820	830.000	1.220
5	600	603.000	0.500
10	430	438.000	1.860
20	330	324.000	-1.818

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

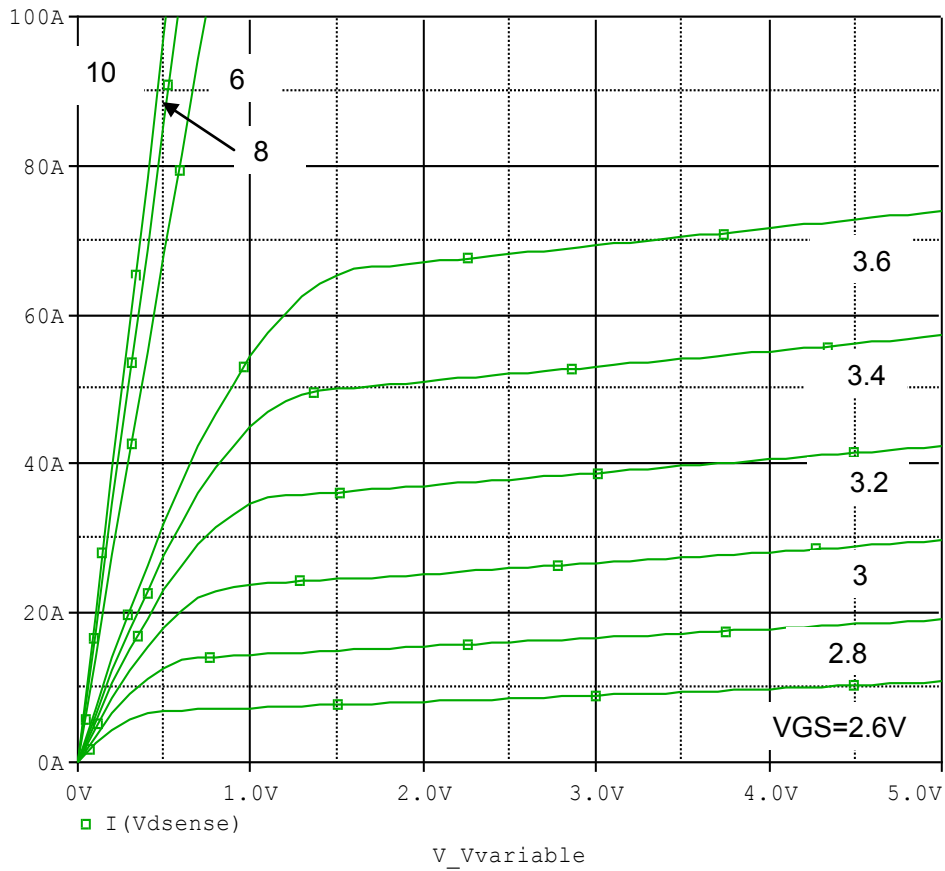


Simulation Result

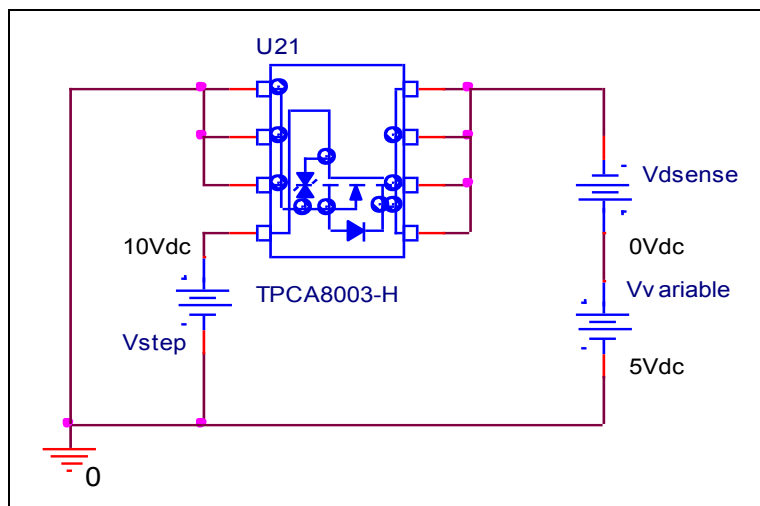
$I_D=18\text{ A}$, $V_{DD}=15\text{ V}$ $V_{GS}=0/10\text{ V}$	Measurement	Simulation	Error(%)
Ton(ns)	11.000	10.965	-0.318

Output Characteristic

Circuit Simulation result



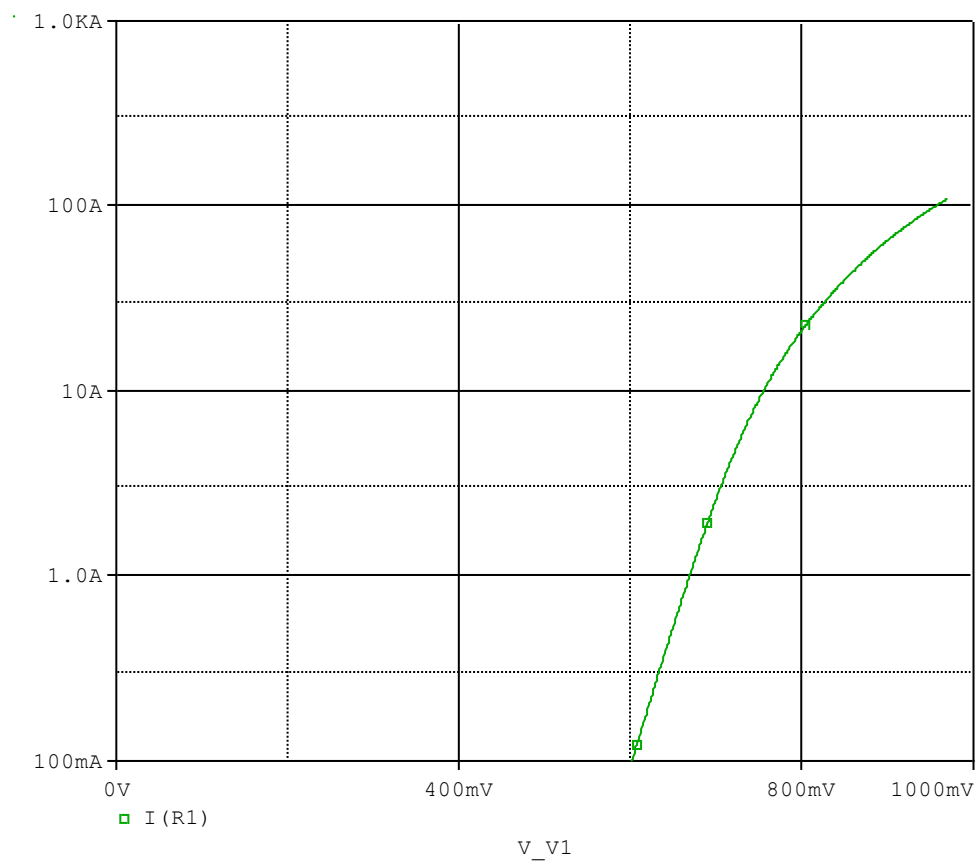
Evaluation circuit



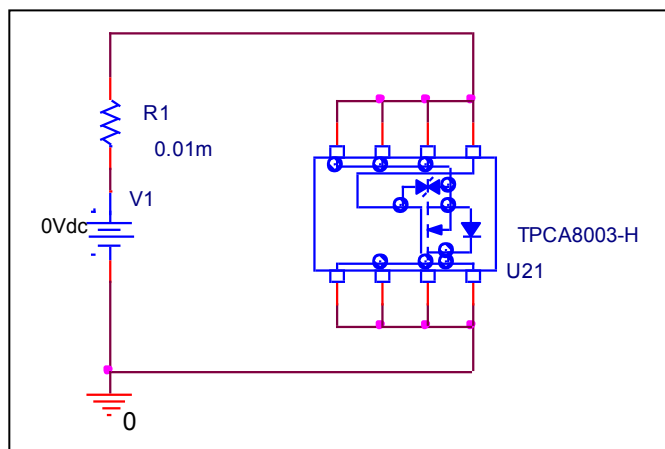
BODY DIODE

Forward Current Characteristic

Circuit Simulation Result

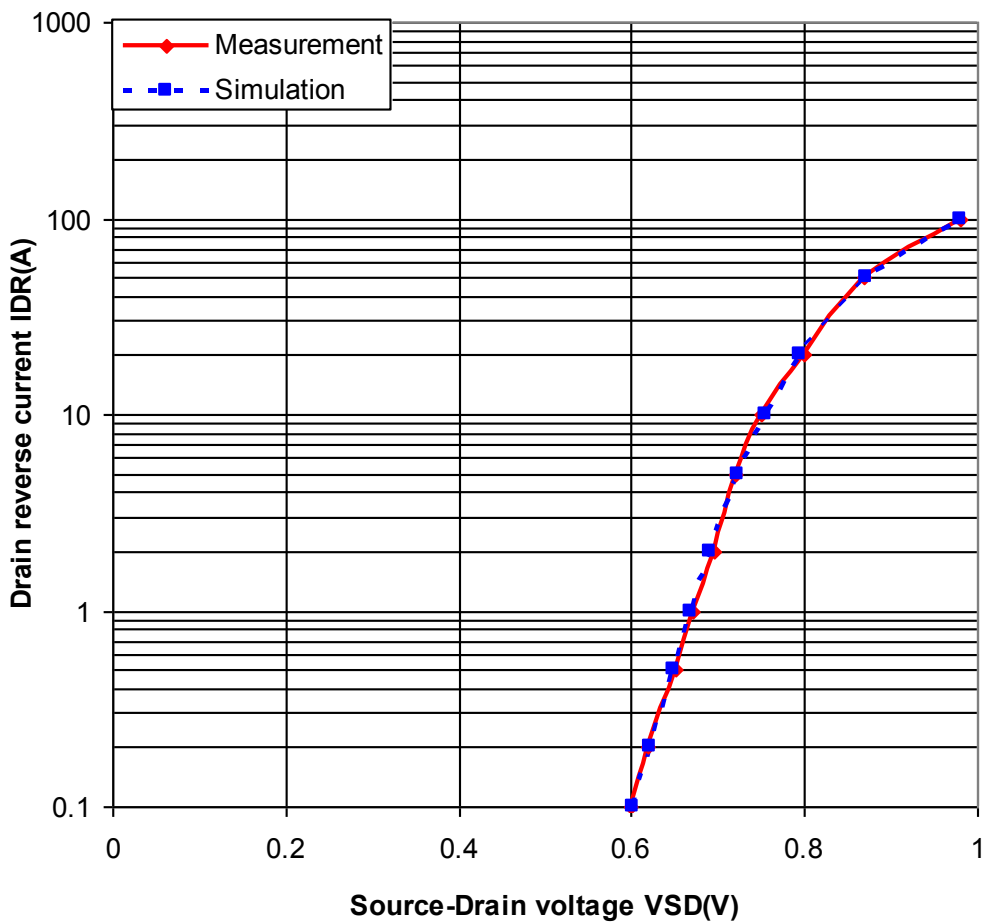


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

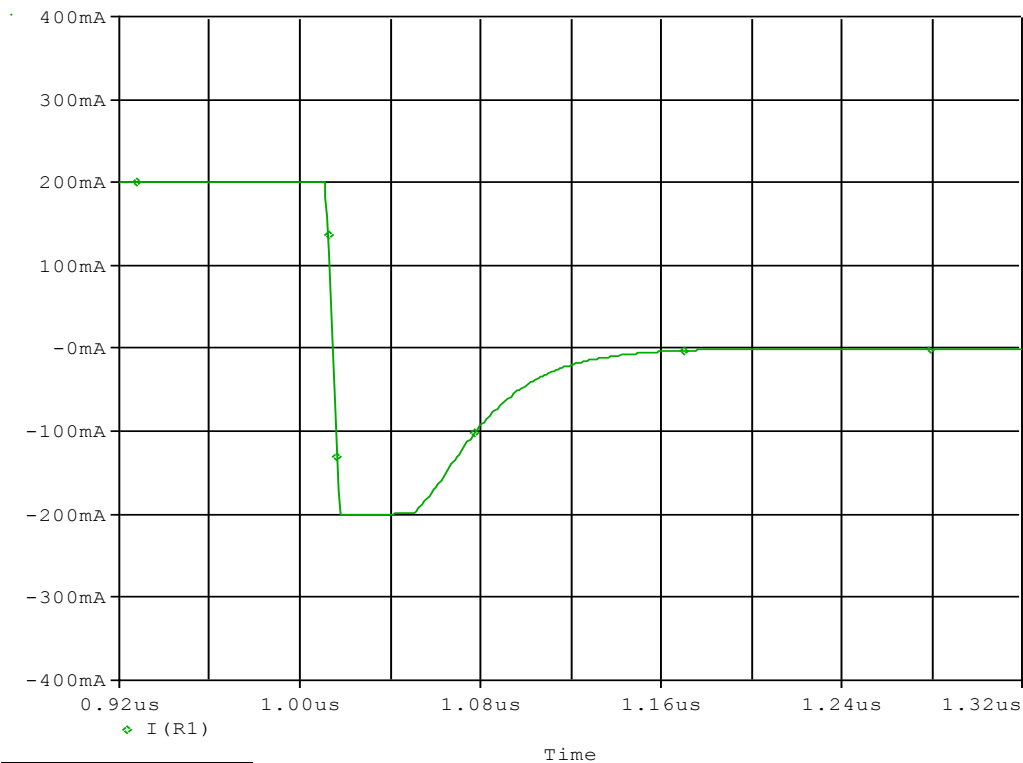


Simulation Result

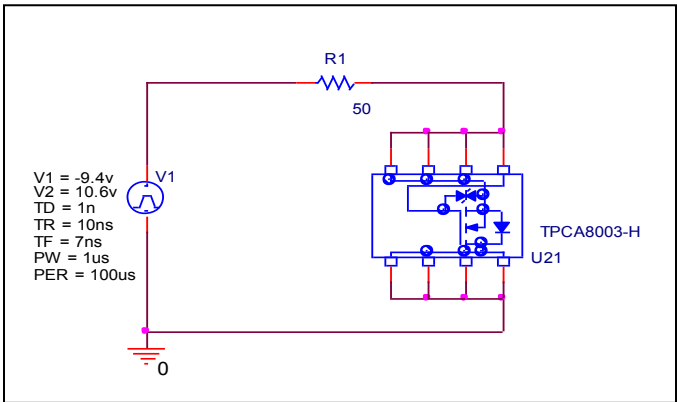
IDR(A)	VSD(V)		%Error
	Measuremen	Simulation	
0.1	0.600	0.601	0.167
0.2	0.620	0.621	0.161
0.5	0.650	0.648	-0.308
1	0.670	0.668	-0.299
2	0.695	0.691	-0.576
5	0.720	0.724	0.556
10	0.750	0.755	0.667
20	0.800	0.795	-0.625
50	0.870	0.871	0.115

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

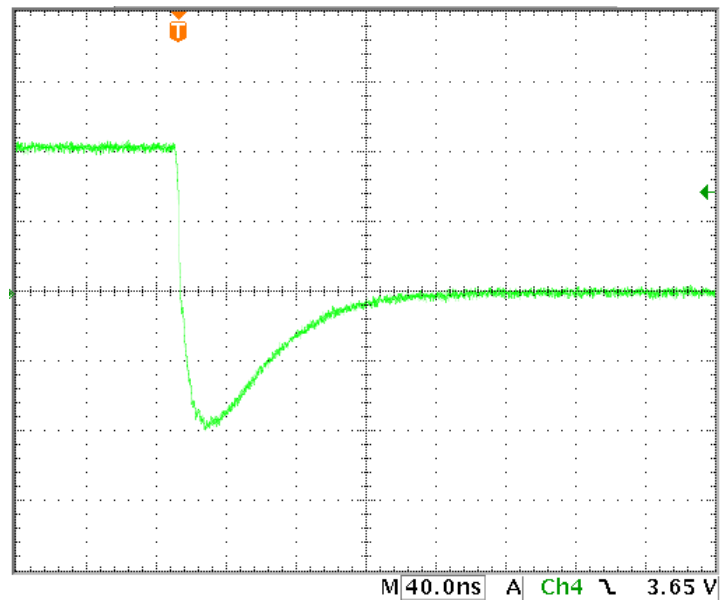


Compare Measurement vs. Simulation

Trr(ns)	Measurement	Simulation	Error (%)
Trj+Trb(ns)	106.000	105.595	-0.382

Reverse Recovery Characteristic

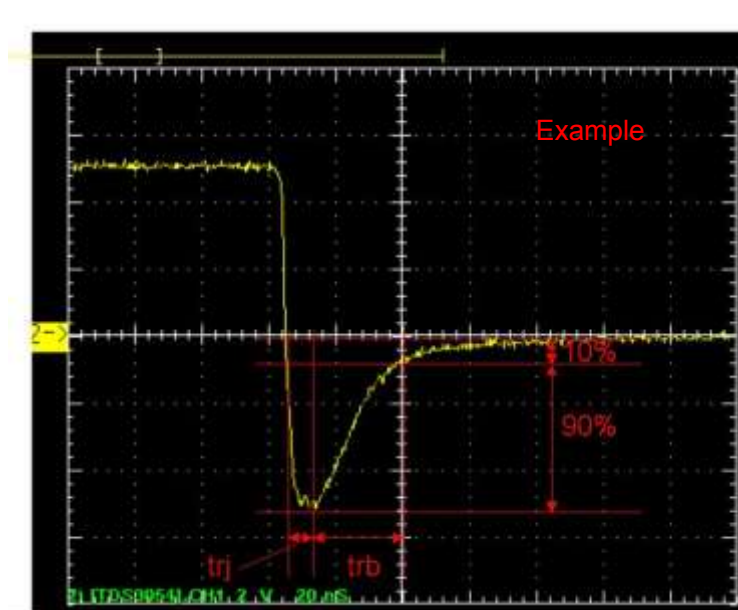
Reference



$T_{rr}=16(\text{ns})$

$T_{rb}=90(\text{ns})$

Conditions: $I_{fwd}=I_{rev}=0.2(\text{A})$, $R_I=50$

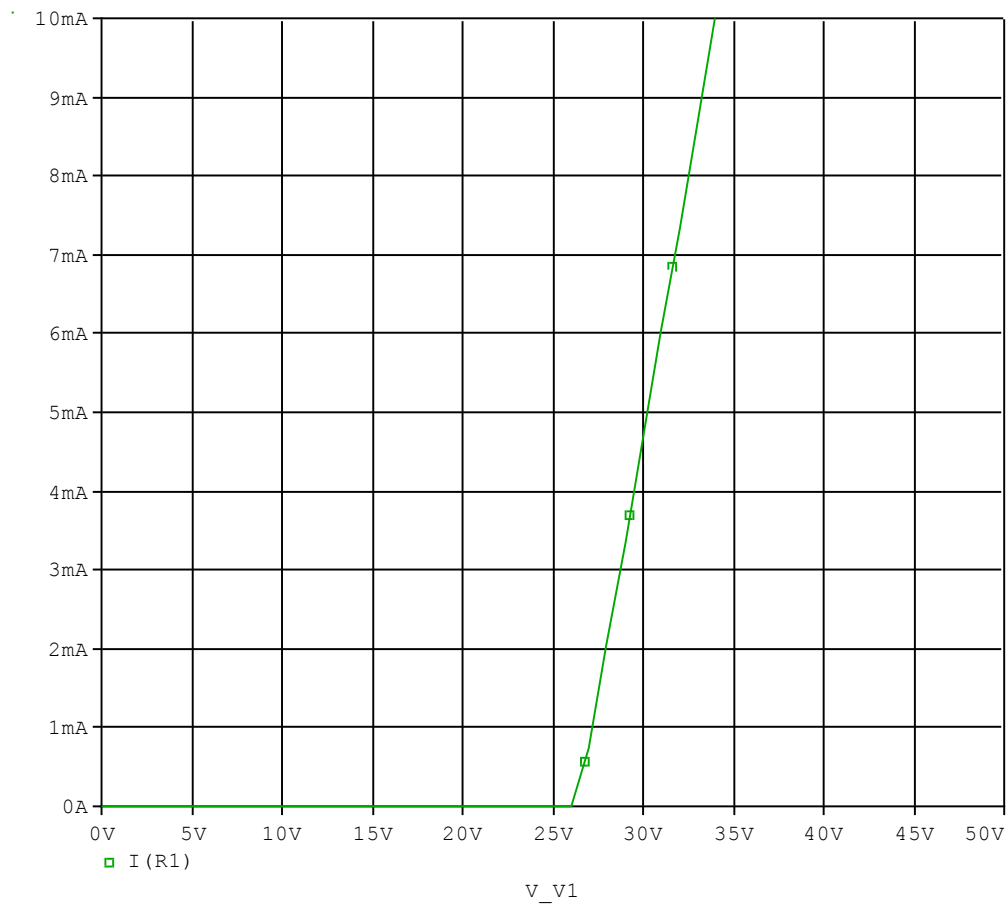


Relation between t_{rr} and t_{rb}

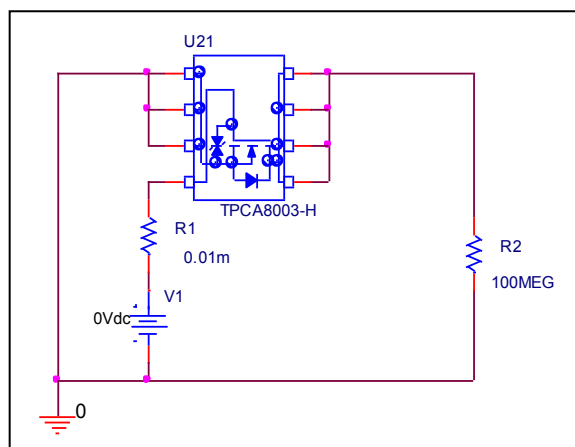
ESD PROTECTION DIODE

Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic

Reference

